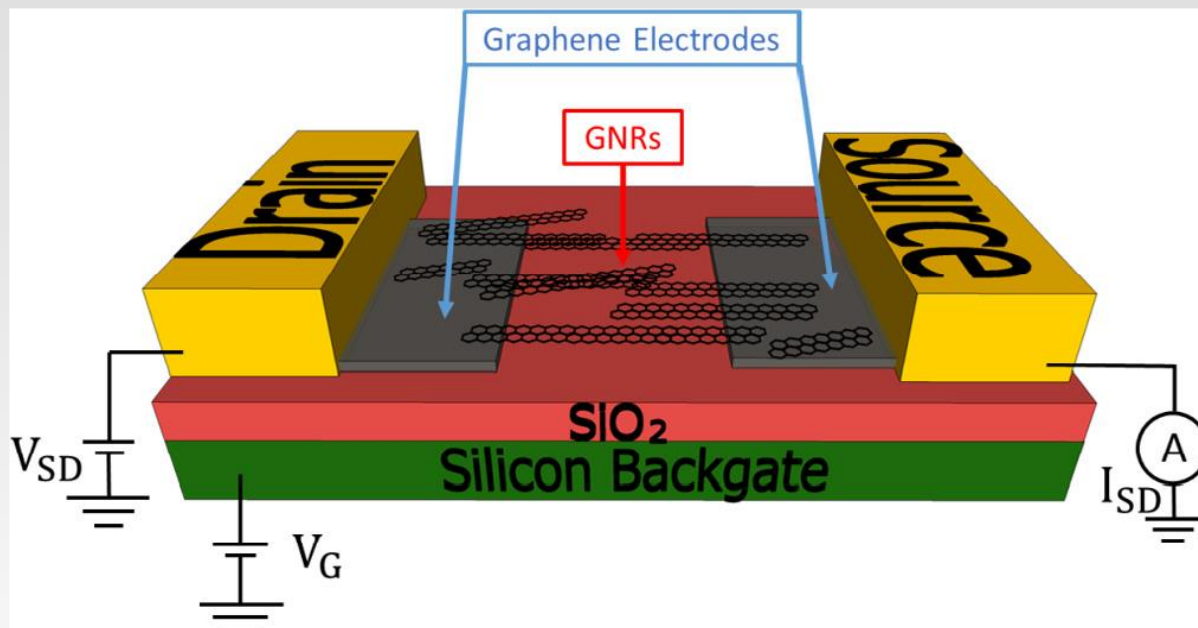


Graphene-based electrodes for graphene nanoribbons devices

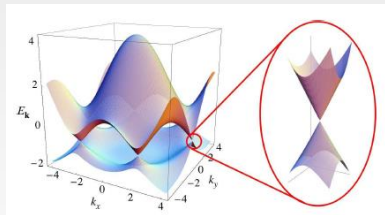
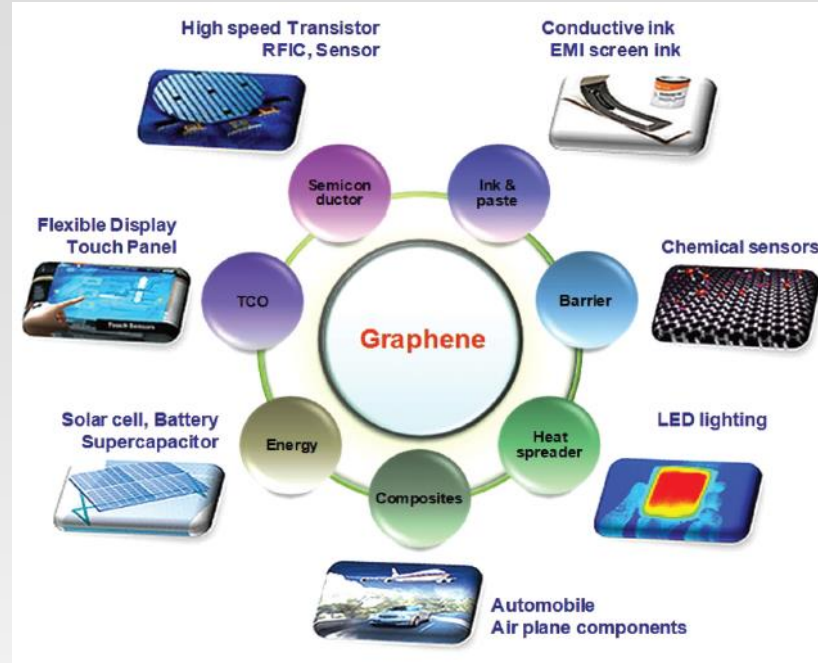


Andrea Candini

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Via Gobetti 101, 40129 Bologna

Motivations

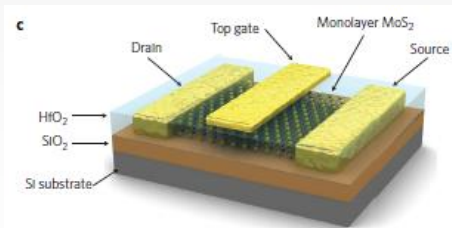
Nanoscale 2015, **7**, 4598



... however... NO Bandgap

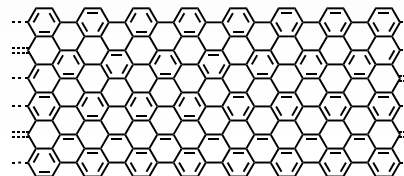


Other materials (2D TMD)



Nature Nanotech. **6**, 147-150 (2011)

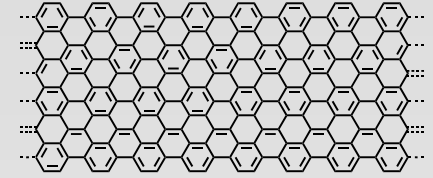
Open a bandgap by structural confinement



see *Rev. Mod. Phys.* **81**, 109-162 (2009)

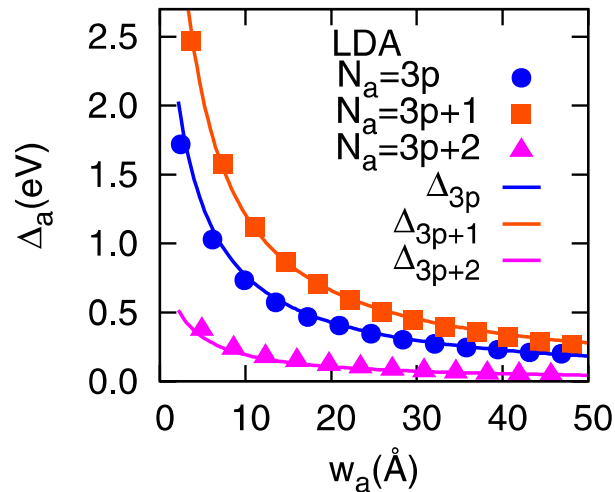
Graphene Nanoribbons (GNRs)

High mobility of graphene + Bandgap
FET and opto-electronic devices



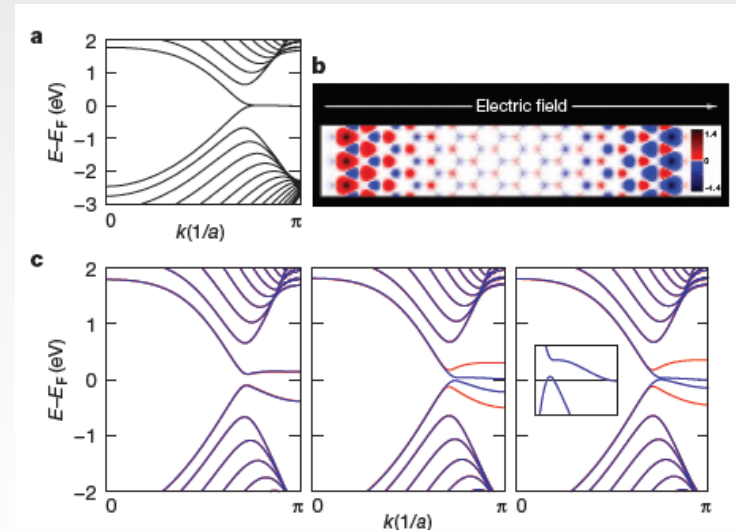
Opto-electrical properties determined by structure

Width-dependent bandgap



Phys. Rev. Lett. **97**,
216803 (2006)

Half-metallic edge states in zGNRs

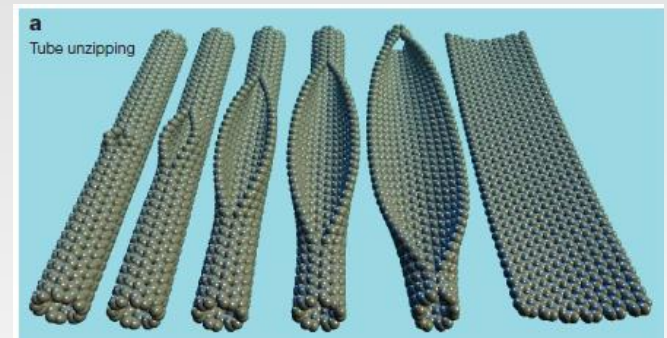
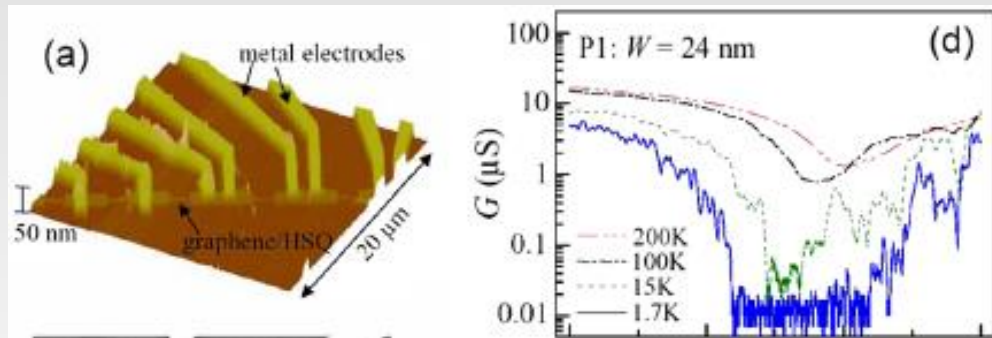


Nature **444**, 347-349
(2006)

GNRs production: Top-Down approaches

Lithography patterning

Carbon nanotube unzipping

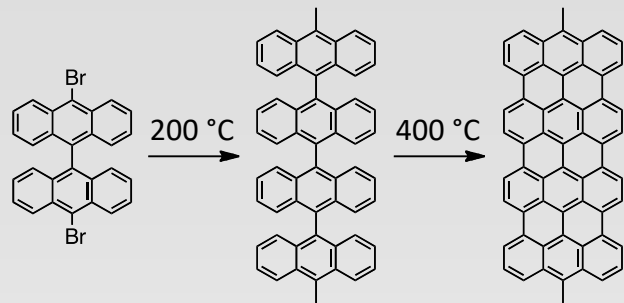


Phys. Rev. Lett. **98**, 206805 (2007)

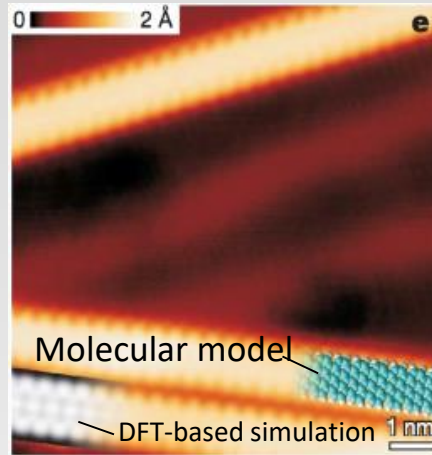
Nature **458**, 872 (2009); 877 (2009)

NO control on width and edge structure

GNRs production: Surface assisted synthesis

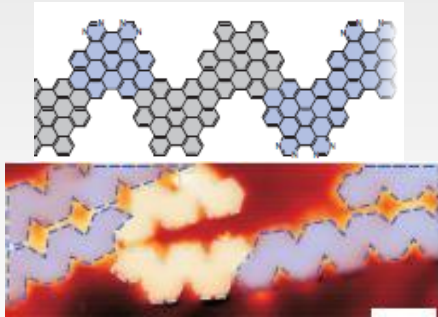


UHV, Au(111) surface



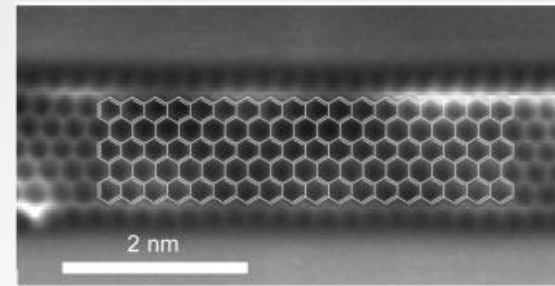
R. Fasel group
K. Müllen group
Nature **466**, 470 (2010)

Heterojunctions



Nature Nanotech. **9**, 896 (2014);
10, 156 (2015)

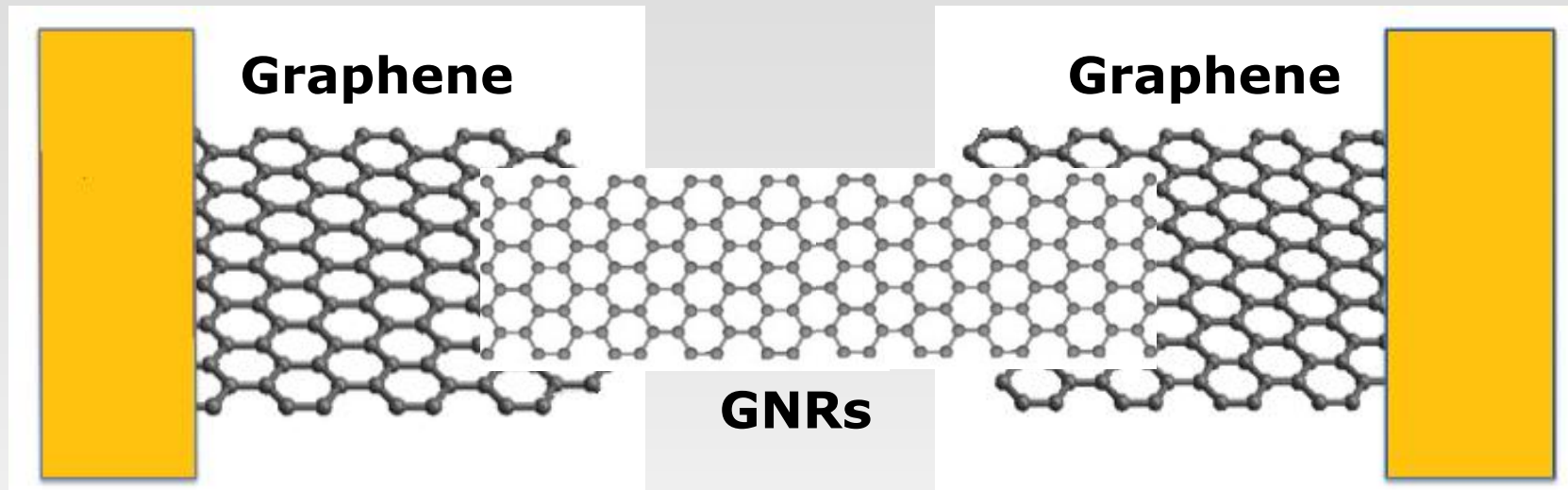
Zigzag edges



Nature **489**, 531 (2016)

Challenge: how to make high-quality devices

All-Graphene Devices



Graphene electrodes - GNRs channel

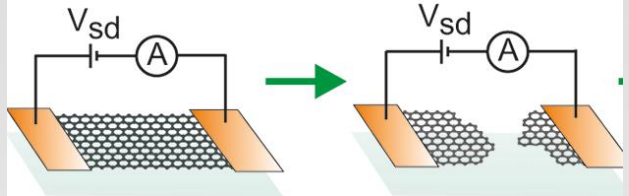
Key points

- Planar and "nano"
- Very stable
- Gatable (no screening)
- Exploit π -stacking

see also E. Lörtscher Nature Nanotechnology **8**, 381 (2013)

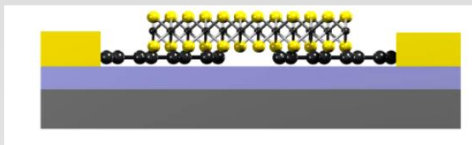
Use of graphene-based electrodes

Single Molecule



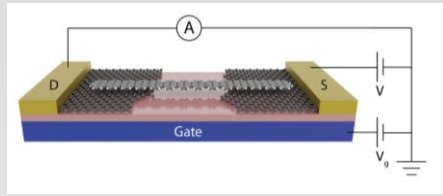
F. Prins et al., Nano Lett 2011
C. Jia et al., Science 2016

other 2D materials



Y. Liu et al.,
Nano Lett. 2015

GNRs

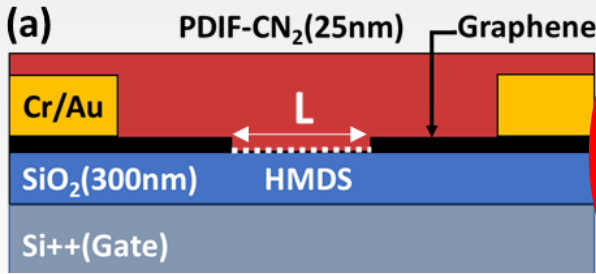


M. El Alabassi et al.,
Nano Lett. 2015

Delft group

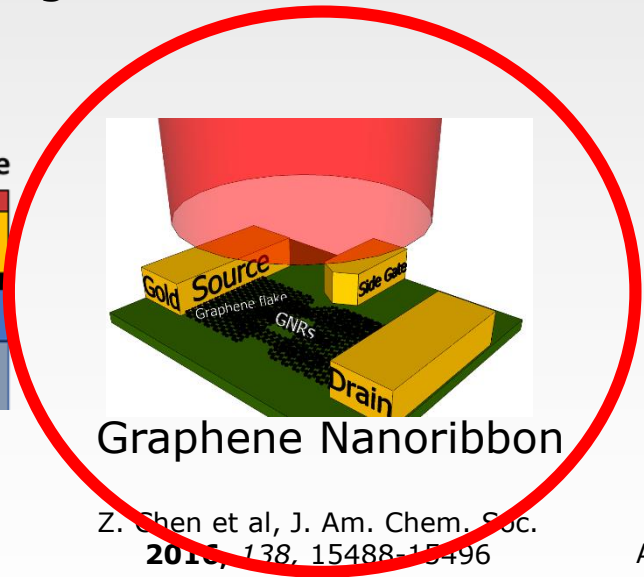
...also Basel, Oxford, Erlangen etc...

... our group



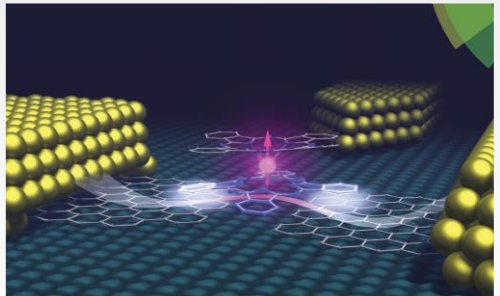
Organic Semiconductor

F. Chianese et al. Appl. Phys. Lett. 112, 213301 (2018)
F. Chianese et al. J. Mat Chem C 8, 8145-8154 (2020)
F. Chianese et al. Synthetic Metals 273, 116683 (2021)



Graphene Nanoribbon

Z. Chen et al, J. Am. Chem. Soc. **2015**, 138, 15488-15496
A. Candini et al, J. Phys. Chem. C **2017**, 121, 10620-10625
L. Martini et al, Carbon **2019**, 146, 36-43



Single (magnetic) molecule

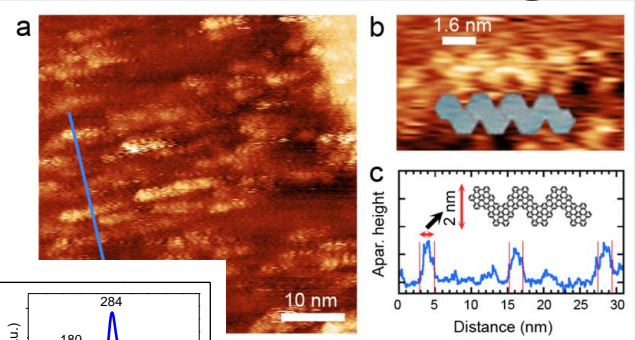
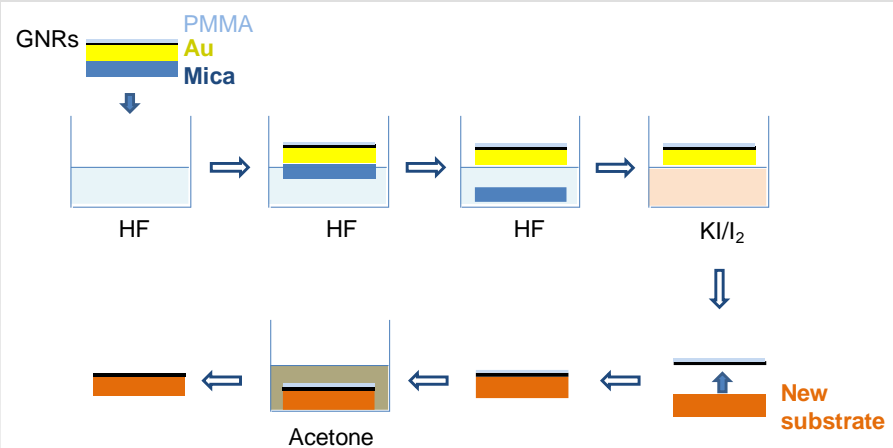
A. Candini et al., Beilstein J. Nanotech. **6**, 711 (2015)
S. Lumetti et al., Dalton Trans. 2016, **45** 16570-16574

GNR growth by CVD

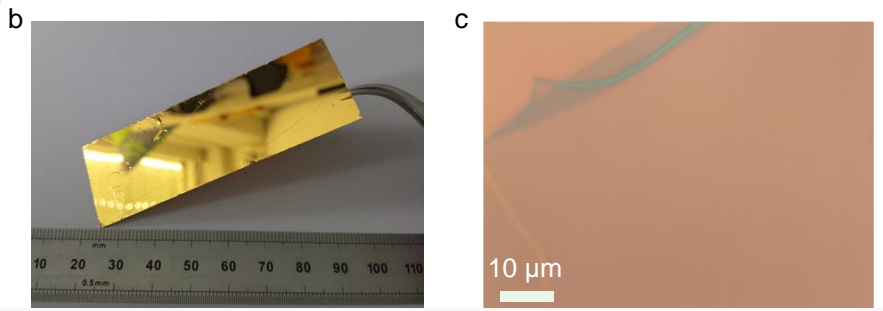
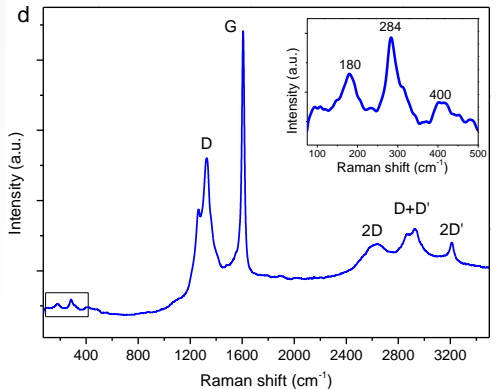
A. Narita, X. Feng, K. Muellen, MPI Mainz and TU Dresden



STM

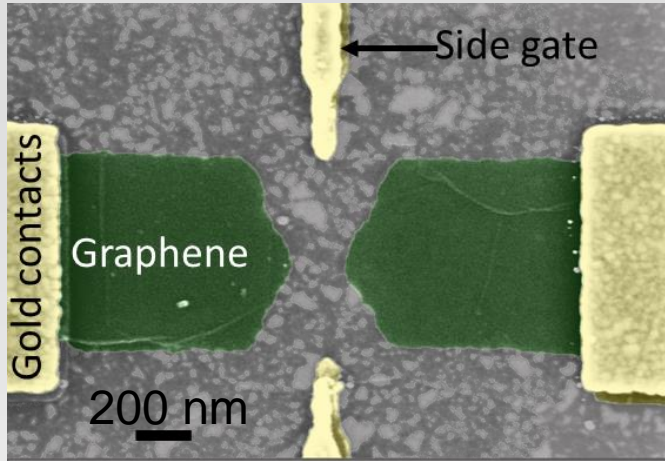


RAMAN

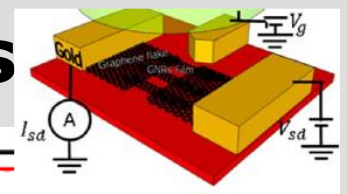
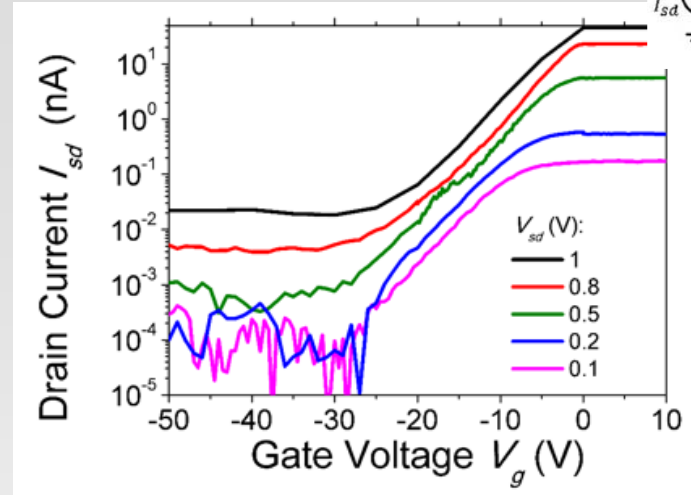


GNRs layer transferred directly on graphene electrodes

GNR devices: thin film optoelectronics

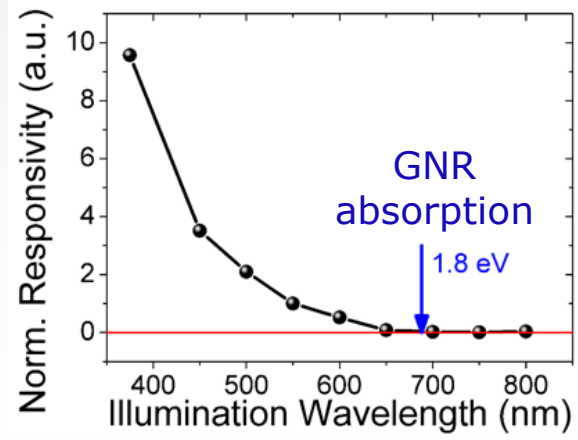
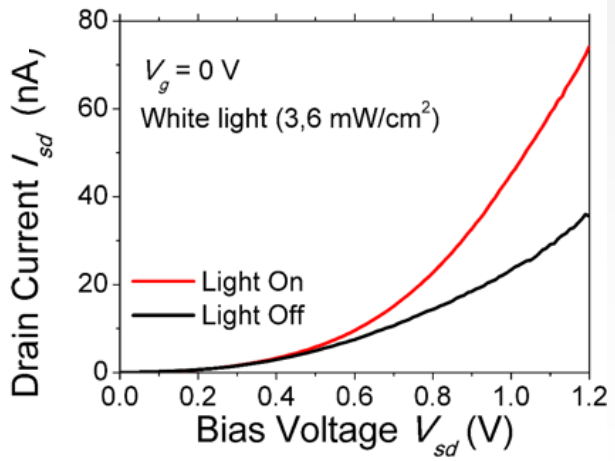


C. Coletti group, IIT Pisa

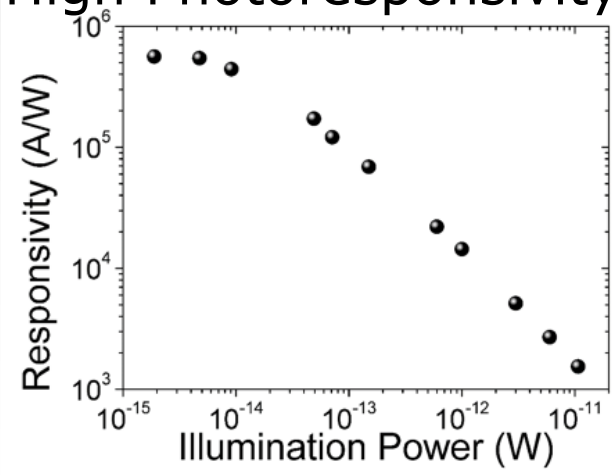


FET behavior $I_{on}/I_{off} \sim 10^4$

Photocurrent

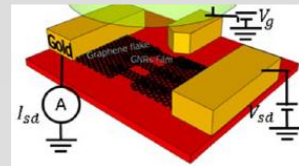


High Photoresponsivity

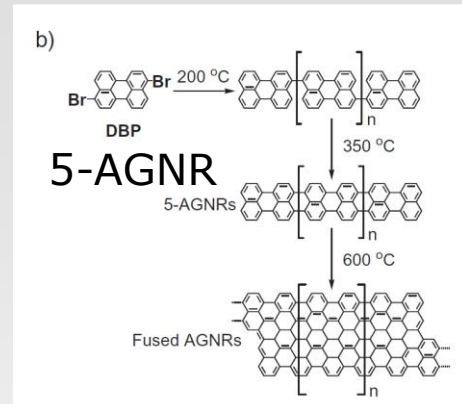
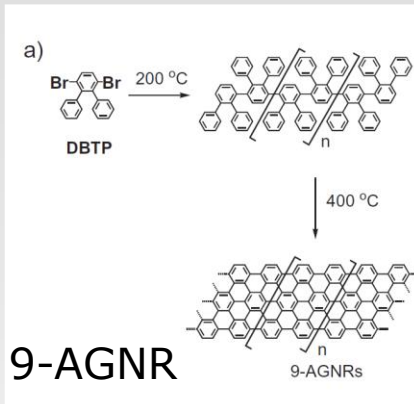


A. Candini et al, *J. Phys. Chem. C* **2017**, 121, 10620-10625

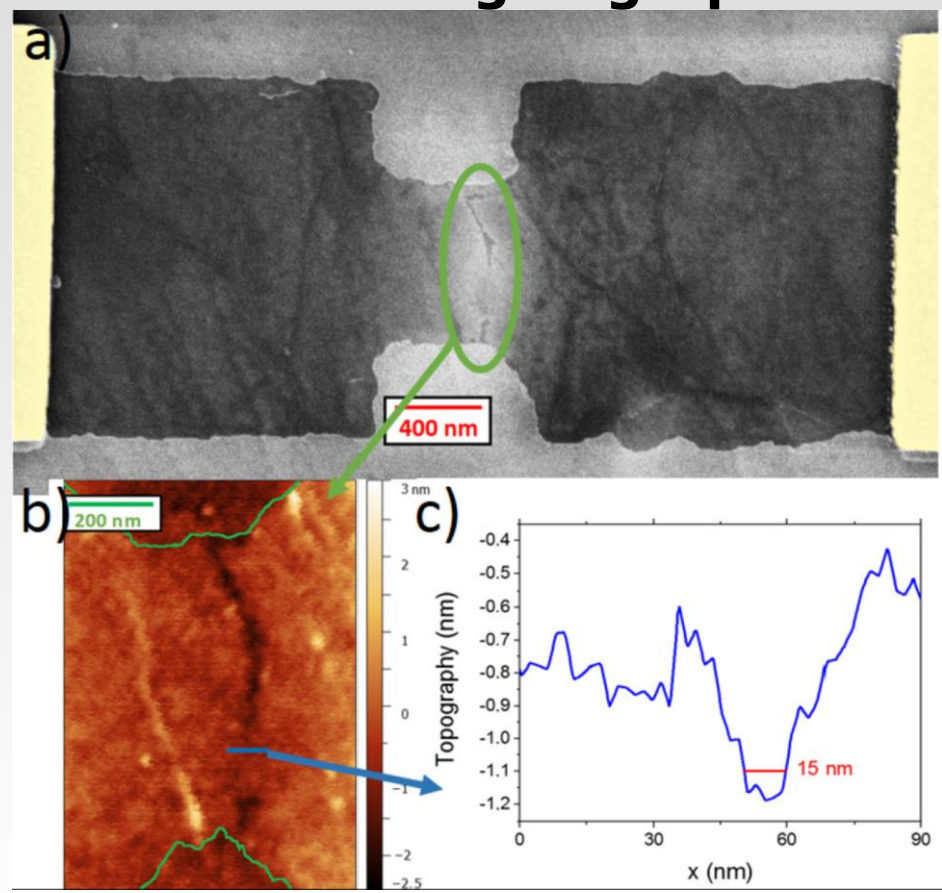
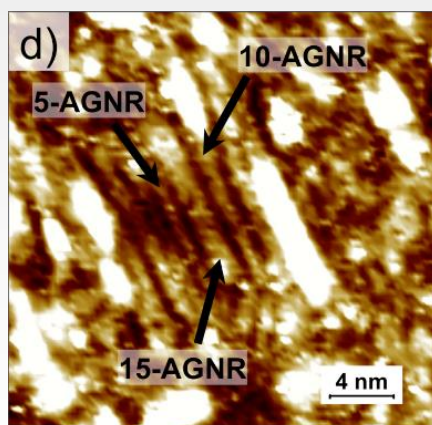
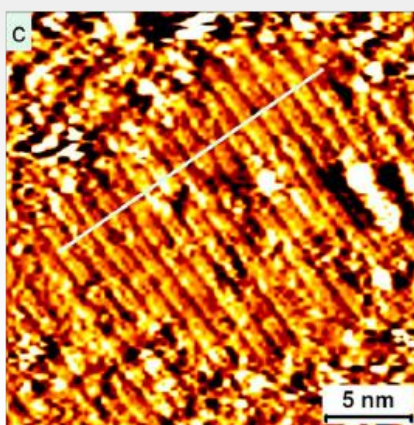
GNR devices: Structure ↔ Electrical Properties



Electroburning of graphene



10,15,20-AGNR



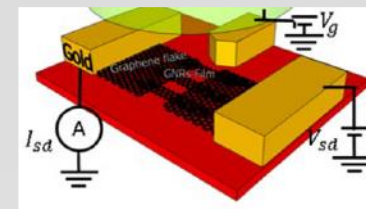
electrode separation \sim 10-20 nm

Z. Chen et al JACS **2017**, 139, 3635

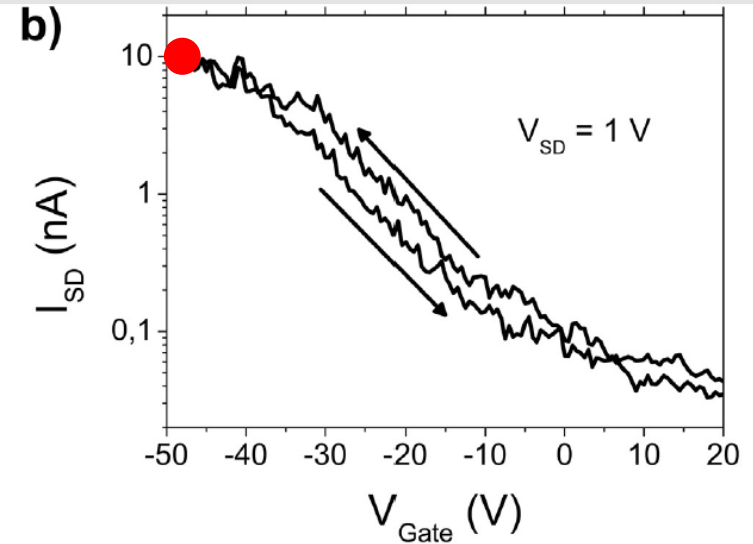
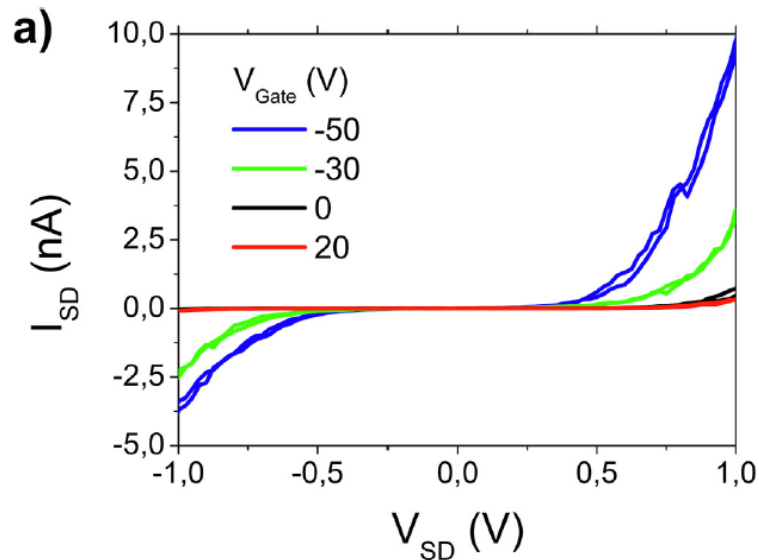
Z. Chen et al JACS **2017**, 139, 9483

L. Martini et al, Carbon **2019**, 146, 36-43

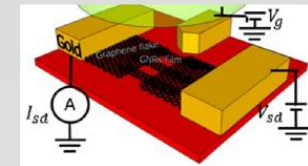
GNR devices: Structure \leftrightarrow Electrical Properties



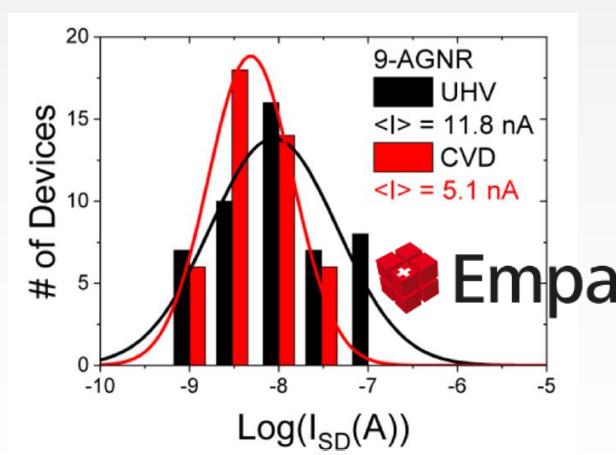
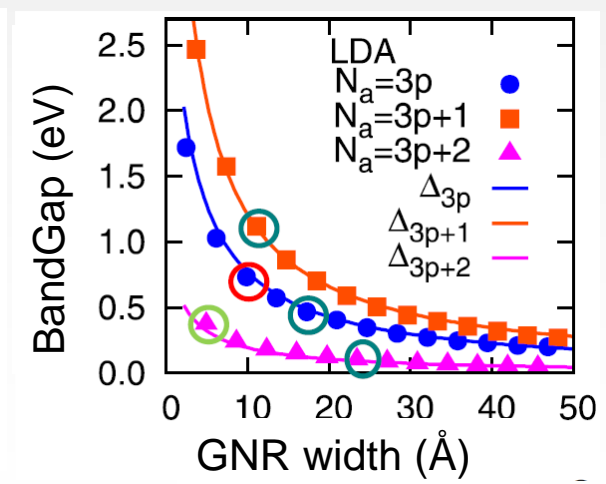
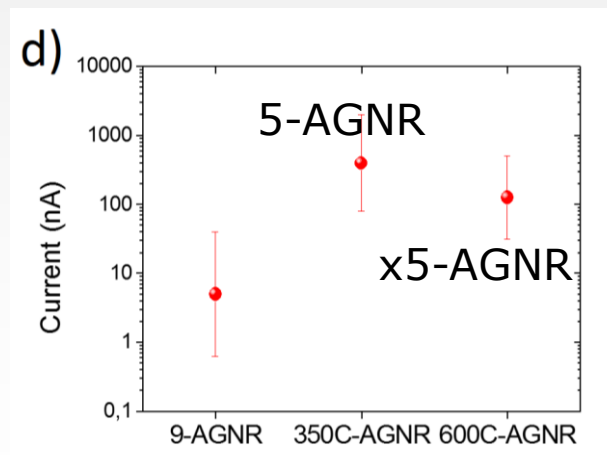
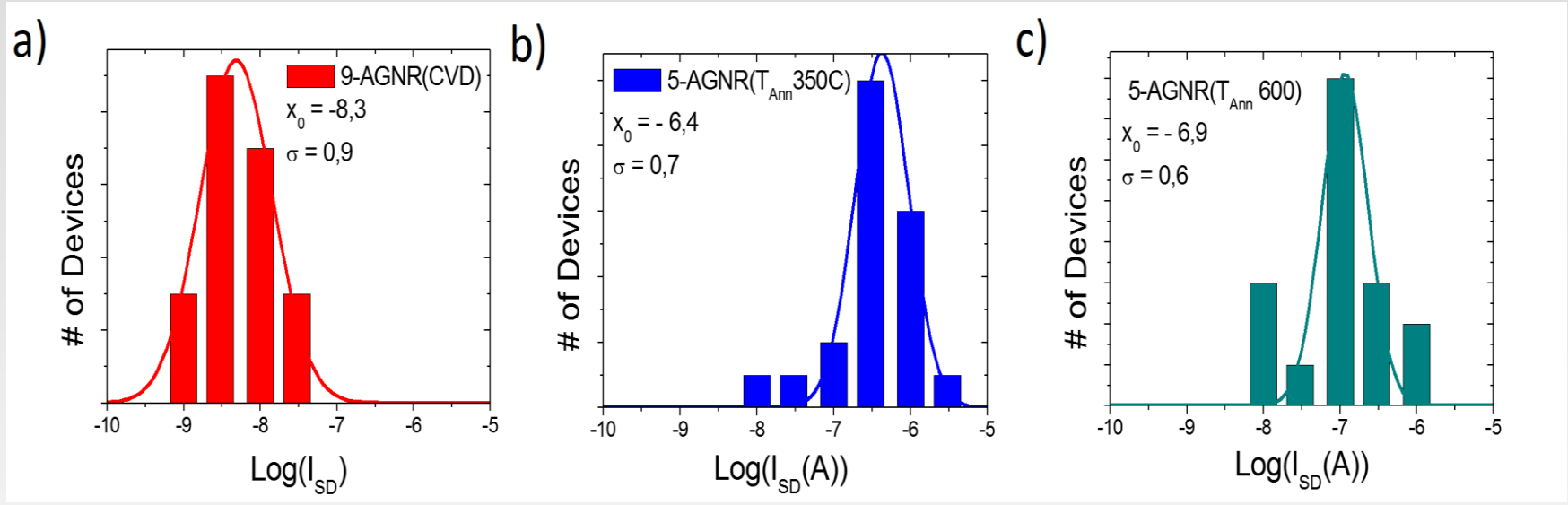
Typical device characteristics



FET behavior, non-linear I-V



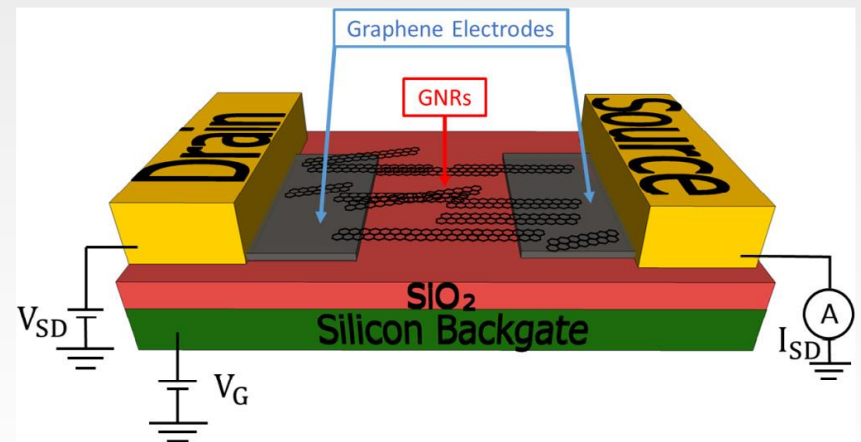
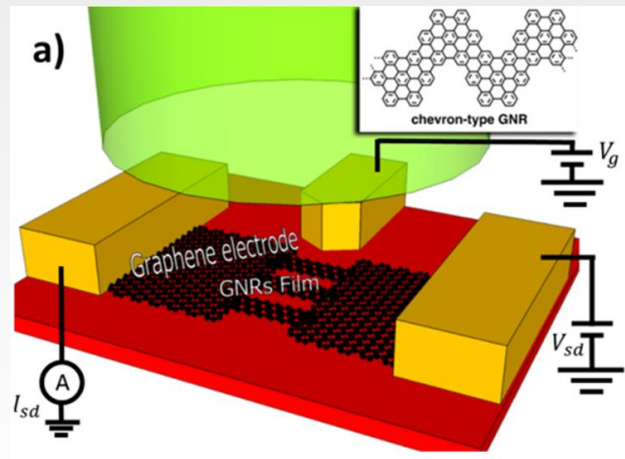
GNR devices: Structure ↔ Electrical Properties



Structure-Properties relation on a device

Conclusions

- All graphene devices (G+GNRs): nanoelectronics and optoelectronics
- Relation between the GNR structure and the device electrical properties



Z. Chen et al, *J. Am. Chem. Soc.* **2016**, *138*, 15488-15496

A. Candini et al, *J. Phys. Chem. C* **2017**, *121*, 10620-10625

L. Martini et al, *Carbon* **2019**, *146*, 36-43

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Domenica Convertino
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Camilla Coletti



Max Planck Institut, Mainz Germany

Zongpeng Chen
Klaus Müllen
Akimitsu Narita



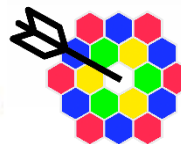
TU Dresden, Dresden, Germany

Xinliang Feng



EMPA - Zurich, Swiss

Gabriela Borin Barin
Pascal Ruffieux
Roman Fasel



ULTIMATE
ITN NETWORK



GRAPHENE FLAGSHIP

